

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#14/Donohoe & Co
Atty
6/6/01

In re application of:

Thomas A. Figura, Kevin Donohoe, & Thomas Dunbar

Serial No.: 09/471,460

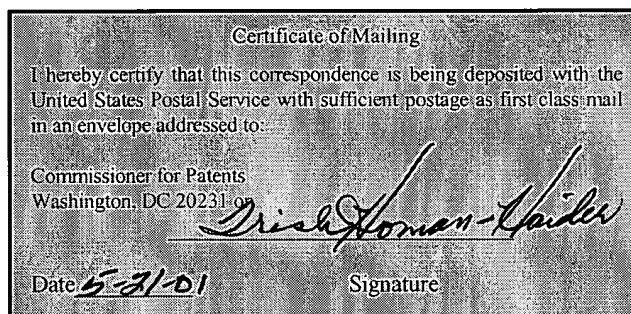
Filed: December 22, 1999

Title: USE OF A PLASMA SOURCE TO FORM A LAYER
DURING THE FORMATION OF A SEMICONDUCTOR DEVICE

§
§ Group Art Unit: 2825
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§ Application Examiner: Calvin Lee
§
§ Atty. Docket: 94-0280.03
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AMENDMENT AND RESPONSE TO THE
OFFICE ACTION DATED NOVEMBER 21, 2000

Commissioner for Patents
Washington, D.C. 20231



Dear Sir:

Applicants submit this Amendment and Response to the Office Action dated November 21, 2000. Please amend the accompanying continued prosecution application as follows.

IN THE CLAIMS

Please cancel claims 20-22 without prejudice.

Please amend the claims to the following form.

44. (Once amended) A method of providing a polymer between metal features on a wafer, comprising:

performing a deposition on said wafer in a site; and
etching in the same general site used to perform said deposition.

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